CD4532BMS

CMOS 8-Bit Priority Encoder

December 1992

Features

- **High Voltage Type (20V Rating)**
- **Converts From 1 of 8 to Binary**
- **Provides Cascading Feature to Handle Any Number of Inputs**
- **Group Select Indicates One or More Priority Inputs**
- **Standardized Symmetrical Output Characteristics**
- **100% Tested for Quiescent Current at 20V**
- **Maximum Input Current of 1μA at 18V Over Full Package Temperature Range; 100nA at 18V and +25°C**
- **Noise Margin (Over Full Package/Temperature Range)**
  - **0.5V at VDD = 5V**
  - **1.5V at VDD = 10V**
  - **1.5V at VDD = 15V**
- **5V, 10V and 15V Parametric Ratings**
- **Meets All Requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"**

Applications

- **Priority Encoder**
- **Binary or BCD Encoder (Keyboard Encoding)**
- **Floating Point Arithmetic**

Description

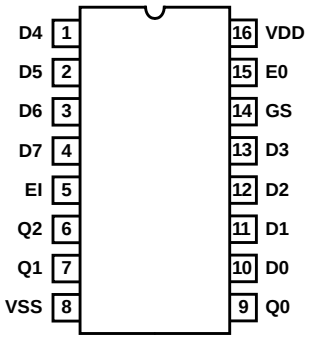
CD4532BMS consists of combinational logic that encodes the highest priority input (D7 - D0) to a 3-bit binary code. The eight inputs, D7 through D0, each have an assigned priority; D7 is the highest priority and D0 is the lowest. The priority encoder is inhibited when the chip-enable input E1 is low. When E1 is high, the binary representation of the highest-priority input appears on output lines Q2 - Q0, and the group select line GS is high to indicate that priority inputs are present. The enable-out (EO) is high when no priority inputs are present. If any one input is high, EO is low and all cascaded lower-order stages are disabled.

The CD4532BMS is supplied in these 16-lead outline packages:

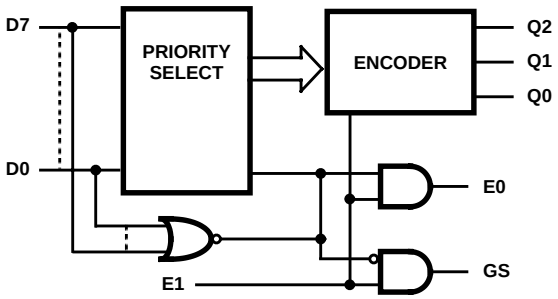
Braze Seal DIP	H4T
Frit Seal DIP	H1E
Ceramic Flatpack	H6W

Pinout

CD4532BMS
TOP VIEW



Functional Diagram



Absolute Maximum Ratings

DC Supply Voltage Range, (VDD) . . . . . -0.5V to +20V
(Voltage Referenced to VSS Terminals)
Input Voltage Range, All Inputs . . . . . .-0.5V to VDD +0.5V
DC Input Current, Any One Input . . . . . .±10mA
Operating Temperature Range . . . . . -55°C to +125°C
Package Types D, F, K, H
Storage Temperature Range (TSTG) . . . . . -65°C to +150°C
Lead Temperature (During Soldering) . . . . . +265°C
At Distance 1/16 ± 1/32 Inch (1.59mm ± 0.79mm) from case for 10s Maximum

Reliability Information

Thermal Resistance	θ_{ja}	θ_{jc}
Ceramic DIP and FRIT Package	80°C/W	20°C/W
Flatpack Package	70°C/W	20°C/W

Maximum Package Power Dissipation (PD) at +125°C
For T_A = -55°C to +100°C (Package Type D, F, K) 500mW
For T_A = +100°C to +125°C (Package Type D, F, K). . . . . Derate Linearity at 12mW/°C to 200mW
Device Dissipation per Output Transistor 100mW
For T_A = Full Package Temperature Range (All Package Types)
Junction Temperature . . . . . +175°C

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS (NOTE 1)		GROUP A SUBGROUPS	TEMPERATURE	LIMITS MIN	LIMITS MAX	UNITS
Supply Current	IDD	VDD = 20V, VIN = VDD or GND		1	+25°C	-	10	µA
				2	+125°C	-	1000	µA
		VDD = 18V, VIN = VDD or GND		3	-55°C	-	10	µA
Input Leakage Current	IIL	VIN = VDD or GND	VDD = 20	1	+25°C	-100	-	nA
				2	+125°C	-1000	-	nA
			VDD = 18V	3	-55°C	-100	-	nA
Input Leakage Current	IIH	VIN = VDD or GND	VDD = 20	1	+25°C	-	100	nA
				2	+125°C	-	1000	nA
			VDD = 18V	3	-55°C	-	100	nA
Output Voltage	VOL15	VDD = 15V, No Load		1, 2, 3	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH15	VDD = 15V, No Load (Note 3)		1, 2, 3	+25°C, +125°C, -55°C	14.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V		1	+25°C	0.53	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V		1	+25°C	1.4	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V		1	+25°C	3.5	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V		1	+25°C	-	-0.53	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V		1	+25°C	-	-1.8	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V		1	+25°C	-	-1.4	mA
Output Current (Source)	IOH15	VDD = 15V, VOUT = 13.5V		1	+25°C	-	-3.5	mA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10µA		1	+25°C	-2.8	-0.7	V
P Threshold Voltage	VPTH	VSS = 0V, IDD = 10µA		1	+25°C	0.7	2.8	V
Functional	F	VDD = 2.8V, VIN = VDD or GND		7	+25°C	VOH > VDD/2	VOL < VDD/2	V
		VDD = 20V, VIN = VDD or GND		7	+25°C			
		VDD = 18V, VIN = VDD or GND		8A	+125°C			
		VDD = 3V, VIN = VDD or GND		8B	-55°C			
Input Voltage Low (Note 2)	VIL	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	+25°C, +125°C, -55°C	-	1.5	V
Input Voltage High (Note 2)	VIH	VDD = 5V, VOH > 4.5V, VOL < 0.5V		1, 2, 3	+25°C, +125°C, -55°C	3.5	-	V
Input Voltage Low (Note 2)	VIL	VDD = 15V, VOH > 13.5V, VOL < 1.5V		1, 2, 3	+25°C, +125°C, -55°C	-	4	V
Input Voltage High (Note 2)	VIH	VDD = 15V, VOH > 13.5V, VOL < 1.5V		1, 2, 3	+25°C, +125°C, -55°C	11	-	V

NOTES: 1. All voltages referenced to device GND, 100% testing being implemented.
2. Go/No Go test with limits applied to inputs.
3. For accuracy, voltage is measured differentially to VDD. Limit is 0.050V max.

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS (NOTE 1, 2)	GROUP A SUBGROUPS	TEMPERATURE	LIMITS MIN	LIMITS MAX	UNITS
Propagation Delay E1 to E0 E1 to GS	TPHL1 TPLH1	VDD = 5V, VIN = VDD or GND	9	+25°C	-	220	ns
			10, 11	+125°C, -55°C	-	297	ns
Propagation Delay E1 to QM DN to GS	TPHL2 TPLH2	VDD = 5V, VIN = VDD or GND	9	+25°C	-	340	ns
			10, 11	+125°C, -55°C	-	459	ns
Propagation Delay DN to QM	TPHL3 TPLH3	VDD = 5V, VIN = VDD or GND	9	+25°C	-	440	ns
			10, 11	+125°C, -55°C	-	594	ns
Transition Time	TTHL TTLH	VDD = 5V, VIN = VDD or GND	9	+25°C	-	200	ns
			10, 11	+125°C, -55°C	-	270	ns

NOTES:

1. CL = 50pF, RL = 200K, Input TR, TF < 20ns.
2. -55°C and +125°C limits guaranteed, 100% testing being implemented.

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS MIN	LIMITS MAX	UNITS
Supply Current	IDD	VDD = 5V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	5	µA
				+125°C	-	150	µA
		VDD = 10V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	10	µA
				+125°C	-	300	µA
		VDD = 15V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	10	µA
				+125°C	-	600	µA
Output Voltage	VOL	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOL	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	4.95	-	V
Output Voltage	VOH	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	9.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V	1, 2	+125°C	0.36	-	mA
				-55°C	0.64	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V	1, 2	+125°C	0.9	-	mA
				-55°C	1.6	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V	1, 2	+125°C	2.4	-	mA
				-55°C	4.2	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V	1, 2	+125°C	-	-0.36	mA
				-55°C	-	-0.64	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V	1, 2	+125°C	-	-1.15	mA
				-55°C	-	-2.0	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V	1, 2	+125°C	-	-0.9	mA
				-55°C	-	-1.6	mA
Output Current (Source)	IOH15	VDD =15V, VOUT = 13.5V	1, 2	+125°C	-	-2.4	mA
				-55°C	-	-4.2	mA
Input Voltage Low	VIL	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	-	3	V

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS MIN	LIMITS MAX	UNITS
Input Voltage High	VIH	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	+7	-	V
Propagation Delay E1 to E0 E1 to GS	TPHL1 TPLH1	VDD = 10V	1, 2, 3	+25°C	-	110	ns
		VDD = 15V	1, 2, 3	+25°C	-	85	ns
Propagation Delay E1 to QM DN to GS	TPHL2 TPLH2	VDD = 10V	1, 2, 3	+25°C	-	170	ns
		VDD = 15V	1, 2, 3	+25°C	-	125	ns
Propagation Delay DN to QM	TPLH3 TPHL3	VDD = 10V	1, 2, 3	+25°C	-	220	ns
		VDD = 15V	1, 2, 3	+25°C	-	160	ns
Transition Time	TTHL TTLH	VDD = 10V	1, 2, 3	+25°C	-	100	ns
		VDD = 15V	1, 2, 3	+25°C	-	80	ns
Input Capacitance	CIN	Any Input	1, 2	+25°C	-	7.5	pF

NOTES:

1. All voltages referenced to device GND.
2. The parameters listed on Table 3 are controlled via design or process and are not directly tested. These parameters are characterized on initial design release and upon design changes which would affect these characteristics.
3. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS MIN	LIMITS MAX	UNITS
Supply Current	IDD	VDD = 20V, VIN = VDD or GND	1, 4	+25°C	-	25	µA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10µA	1, 4	+25°C	-2.8	-0.2	V
N Threshold Voltage Delta	ΔVTN	VDD = 10V, ISS = -10µA	1, 4	+25°C	-	±1	V
P Threshold Voltage	VTP	VSS = 0V, IDD = 10µA	1, 4	+25°C	0.2	2.8	V
P Threshold Voltage Delta	ΔVTP	VSS = 0V, IDD = 10µA	1, 4	+25°C	-	±1	V
Functional	F	VDD = 18V, VIN = VDD or GND	1	+25°C	VOH > VDD/2	VOL < VDD/2	V
		VDD = 3V, VIN = VDD or GND					
Propagation Delay Time	TPHL TPLH	VDD = 5V	1, 2, 3, 4	+25°C	-	1.35 x +25°C Limit	ns

NOTES: 1. All voltages referenced to device GND.
2. CL = 50pF, RL = 200K, Input TR, TF < 20ns.
3. See Table 2 for +25°C limit.
4. Read and Record

TABLE 5. BURN-IN AND LIFE TEST DELTA PARAMETERS +25°C

PARAMETER	SYMBOL	DELTA LIMIT
Supply Current - MSI-2	IDD	± 1.0µA
Output Current (Sink)	IOL5	± 20% x Pre-Test Reading
Output Current (Source)	IOH5A	± 20% x Pre-Test Reading

TABLE 6. APPLICABLE SUBGROUPS

CONFORMANCE GROUP		MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD
Initial Test (Pre Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 1 (Post Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 2 (Post Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note 1)		100% 5004	1, 7, 9, Deltas	
Interim Test 3 (Post Burn-In)		100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note 1)		100% 5004	1, 7, 9, Deltas	
Final Test		100% 5004	2, 3, 8A, 8B, 10, 11	
Group A		Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11	
Group B	Subgroup B-5	Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11, Deltas	Subgroups 1, 2, 3, 9, 10, 11
	Subgroup B-6	Sample 5005	1, 7, 9	
Group D		Sample 5005	1, 2, 3, 8A, 8B, 9	Subgroups 1, 2 3

NOTE: 1. 5% Parameteric, 3% Functional; Cumulative for Static 1 and 2.

TABLE 7. TOTAL DOSE IRRADIATION

CONFORMANCE GROUPS	MIL-STD-883 METHOD	TEST		READ AND RECORD	
		PRE-IRRAD	POST-IRRAD	PRE-IRRAD	POST-IRRAD
Group E Subgroup 2	5005	1, 7, 9	Table 4	1, 9	Table 4

TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS

FUNCTION	OPEN	GROUND	VDD	9V ± -0.5V	OSCILLATOR	
					50kHz	25kHz
Static Burn-In 1 (Note 1)	6, 7, 9, 14, 15	1 - 5, 8, 10 - 13	16			
Static Burn-In 2 (Note 1)	6, 7, 9, 14, 15	8	1 - 5, 10 - 13, 16			
Dynamic Burn-In (Note 1)	-	8	5, 16	6, 7, 9, 14, 15	1 - 4, 10 - 13	
Irradiation (Note 2)	6, 7, 9, 14, 15	8	1 - 5, 10 - 13, 16			

NOTES:

1. Each pin except VDD and GND will have a series resistor of 10K ± 5%, VDD = 18V ± 0.5V
2. Each pin except VDD and GND will have a series resistor of 47K ± 5%; Group E, Subgroup 2, sample size is 4 dice/wafer, 0 failures, VDD = 10V ± 0.5V

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Logic Diagram

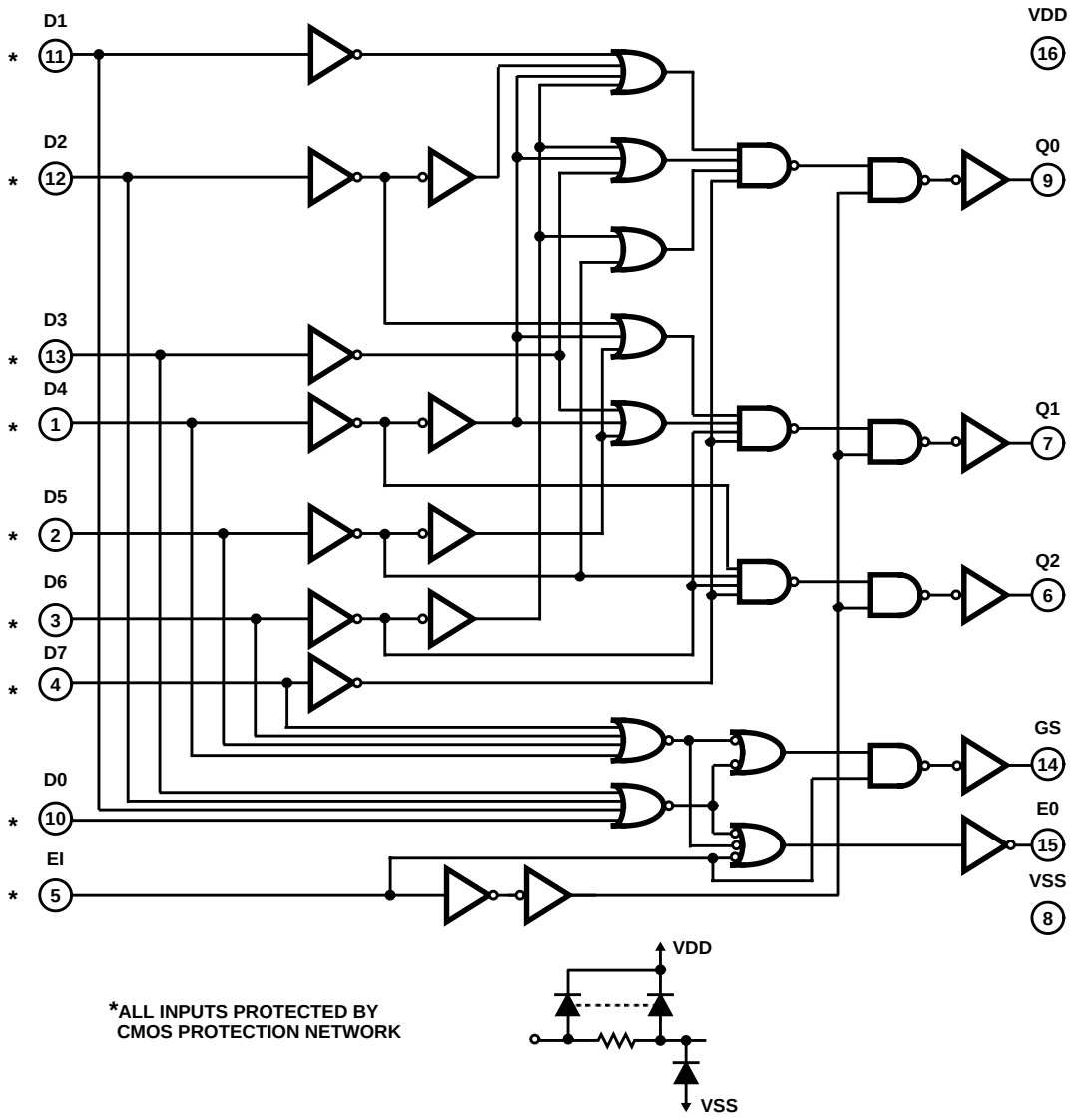


FIGURE 1. CD4532BMS LOGIC DIAGRAM

TRUTH TABLE

INPUT									OUTPUT				
E1	D7	D6	D5	D4	D3	D2	D1	D0	GS	Q2	Q1	Q0	E0
0	X	X	X	X	X	X	X	X	0	0	0	0	0
1	0	0	0	0	0	0	0	0	0	0	0	0	1
1	1	X	X	X	X	X	X	X	1	1	1	1	0
1	0	1	X	X	X	X	X	X	1	1	1	0	0
1	0	0	1	X	X	X	X	X	1	1	0	1	0
1	0	0	0	1	X	X	X	X	1	1	0	0	0
1	0	0	0	0	1	X	X	X	1	0	1	1	0
1	0	0	0	0	0	1	X	X	1	0	1	0	0
1	0	0	0	0	0	0	1	X	1	0	0	1	0
1	0	0	0	0	0	0	0	1	1	0	0	0	0

X = Don't Care Logic 1 ≡ High Logic 0 ≡ Low

Typical Performance Characteristics

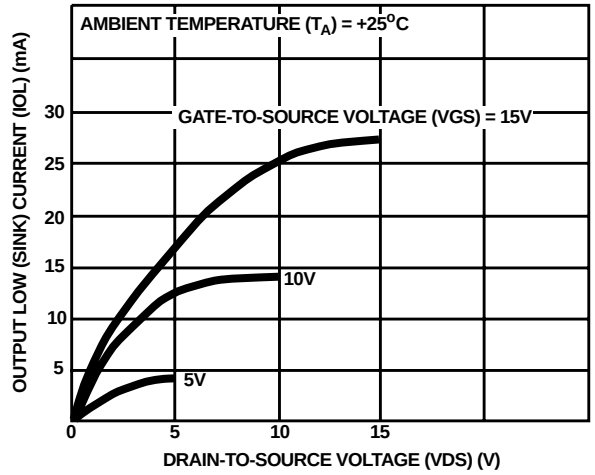


FIGURE 2. TYPICAL OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

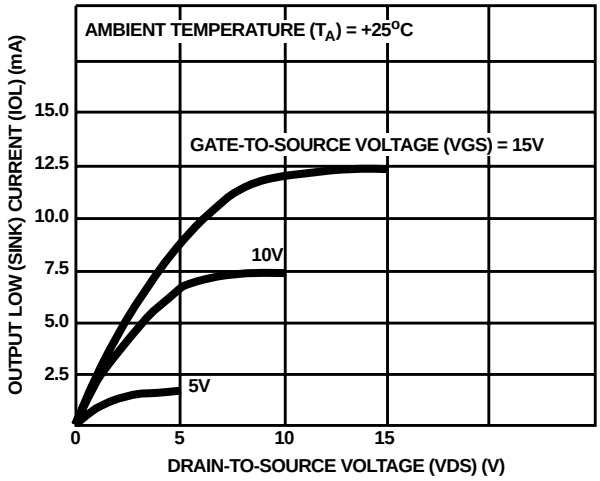


FIGURE 3. MINIMUM OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

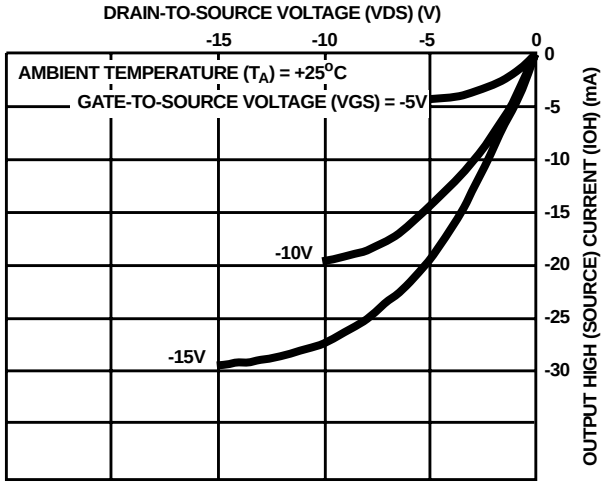


FIGURE 4. TYPICAL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

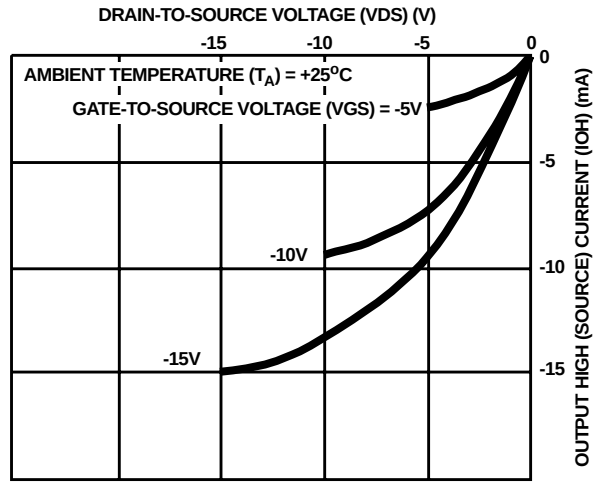


FIGURE 5. MINIMUM OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

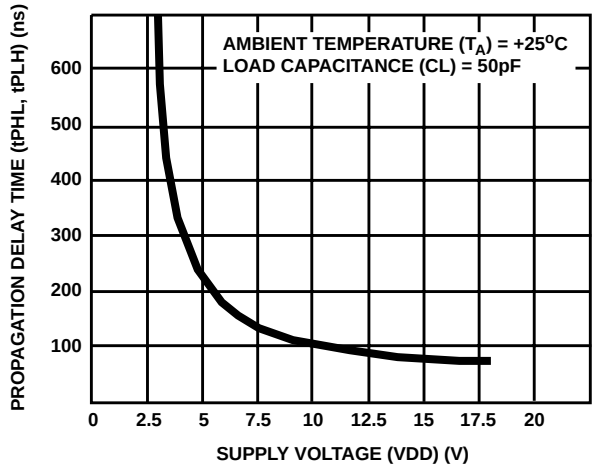


FIGURE 6. TYPICAL PROPAGATION DELAY (DN TO QM) vs SUPPLY VOLTAGE

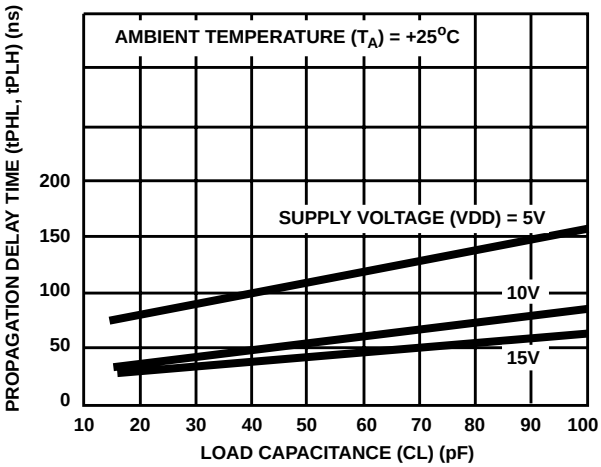


FIGURE 7. TYPICAL PROPAGATION DELAY (E1 TO GS, E1 TO EQ) vs LOAD CAPACITANCE

Typical Performance Characteristics (Continued)

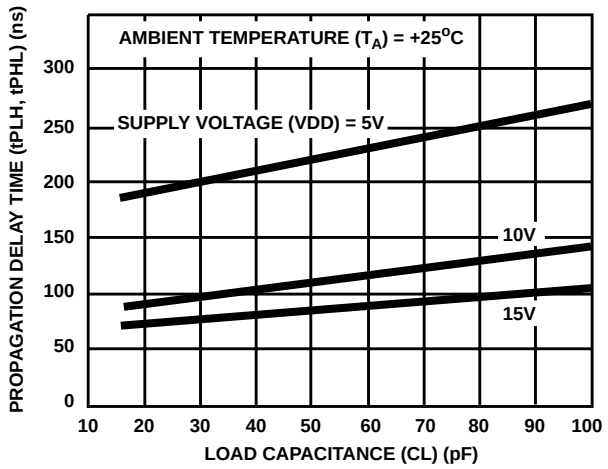


FIGURE 8. TYPICAL PROPAGATION DELAY (DN TO QM) vs LOAD CAPACITANCE

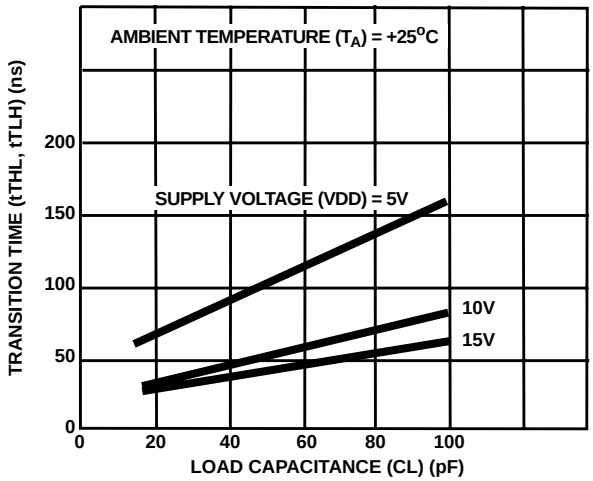


FIGURE 9. TYPICAL TRANSITION TIME vs LOAD CPACITANCE

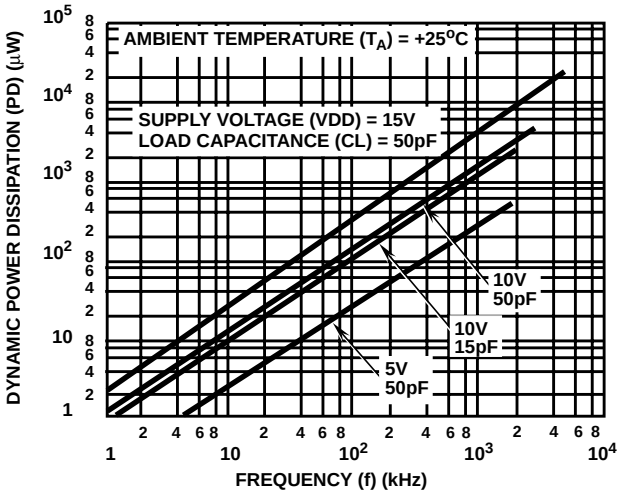


FIGURE 10. TYPICAL DYNAMIC POWER DISSIPATION vs FREQUENCY

Applications

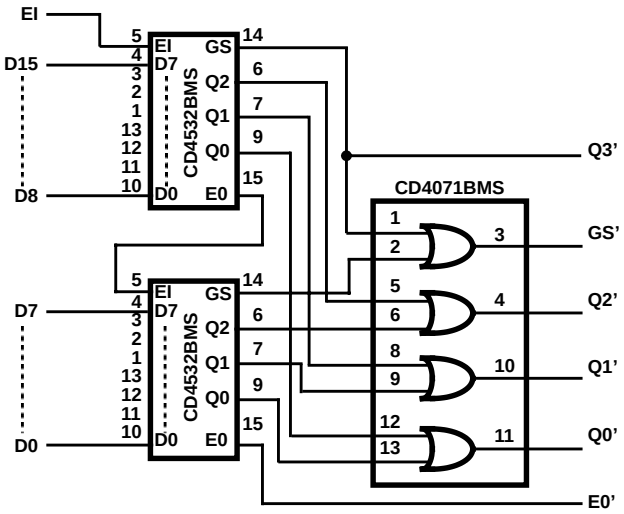


FIGURE 11. 16-LEVEL PRIORITY ENCODER

Applications (Continued)

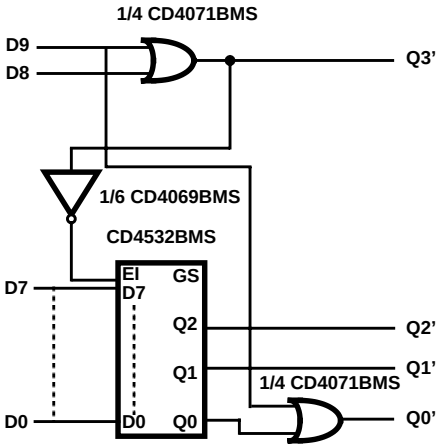


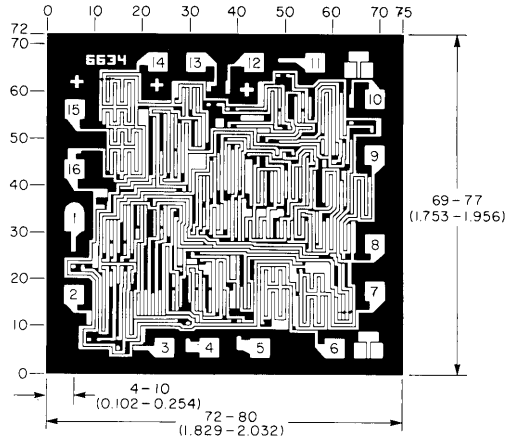
FIGURE 12. 0-TO-9 KEYBOARD ENCODER

TRUTH TABLE

INPUT										OUTPUT				
D9	D8	D7	D6	D5	D4	D3	D2	D1	D0	GS	Q3'	Q2'	Q1'	Q0'
1	X	X	X	X	X	X	X	X	X	0	1	0	0	1
0	1	X	X	X	X	X	X	X	X	0	1	0	0	0
0	0	1	X	X	X	X	X	X	X	1	0	1	1	1
0	0	0	1	X	X	X	X	X	X	1	0	1	1	0
0	0	0	0	1	X	X	X	X	X	1	0	1	0	1
0	0	0	0	0	1	X	X	X	X	1	0	1	0	0
0	0	0	0	0	0	1	X	X	X	1	0	0	1	1
0	0	0	0	0	0	0	1	X	X	1	0	0	1	0
0	0	0	0	0	0	0	0	1	X	1	0	0	0	1
0	0	0	0	0	0	0	0	0	1	1	0	0	0	0

X = Don't Care Logic 1 ≡ High Logic 0 ≡ Low

Chip Dimensions and Pad Layout



Dimensions in parenthesis are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

METALLIZATION: Thickness: 11kÅ – 14kÅ, AL.
PASSIVATION: 10.4kÅ - 15.6kÅ, Silane
BOND PADS: 0.004 inches X 0.004 inches MIN
DIE THICKNESS: 0.0198 inches - 0.0218 inches